

A METHOD OF BASE FORMATION IN A BICMOS PROCESS

Abstract

Disclosed is a bipolar complementary metal oxide semiconductor (BiCMOS) or NPN/PNP device that has a collector, an intrinsic base above the collector, shallow trench isolation regions adjacent the collector, a raised extrinsic base above the intrinsic base, a T-shaped emitter above the extrinsic base, spacers adjacent the emitter, and a silicide layer that is separated from the emitter by the spacers.